

GST2SC3356

High-Frequency Amplifier Transistor NPN Silicon

Product Description

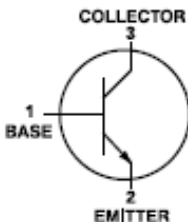
This device is designed as a general purpose amplifier and switch.

Features

- Low noise amplifier at VHF, UHF and CATV band
- Low Noise and High Gain
- High Power Gain
- Lead(Pb)-Free

Packages & Pin Assignments

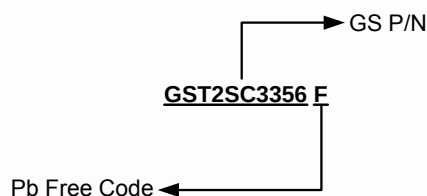
GST2SC3356F(SOT-23)	
	
Pin	Description
1	Base
2	Emitter
3	Collector



Marking Information

P/N	Package	Part Marking
GST2SC3356F	SOT-23	2SC3356

Ordering Information



Part Number	Package	Quantity
GST2SC3356F	SOT-23	3000 PCS

GST2SC3356

Absolute Maximum Ratings

$T_A=25^{\circ}\text{C}$

Symbol	Conditions	Value	Unit
V_{CEO}	Collector-Emitter Voltage	12	V
V_{CBO}	Collector-Base Voltage	20	V
V_{EBO}	Emitter-Base Voltage	3	V
I_C	Collector Current-Continuous	0.1	A
P_D	Collector Power Dissipation	0.25	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$

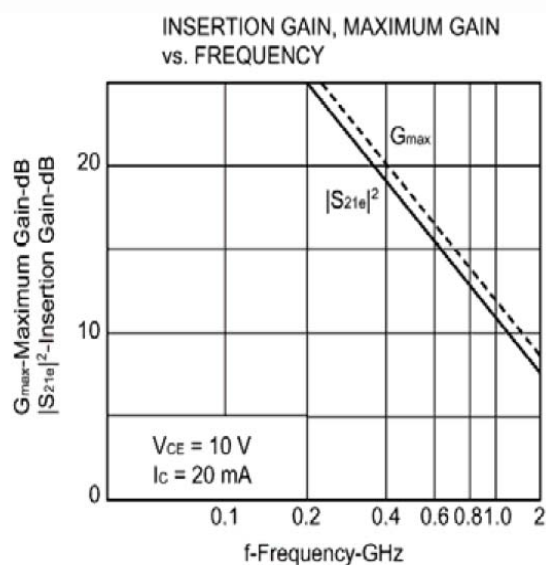
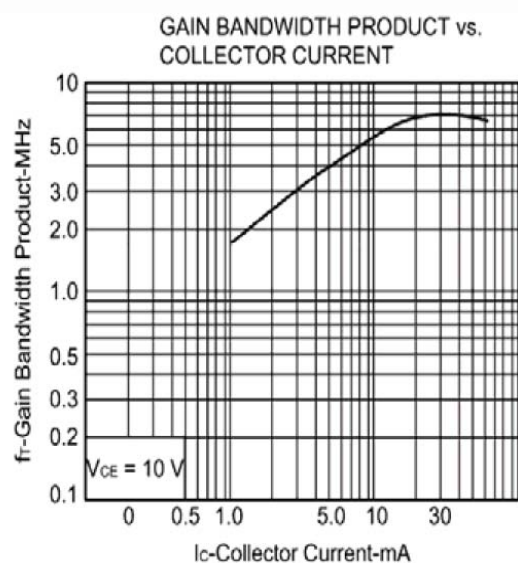
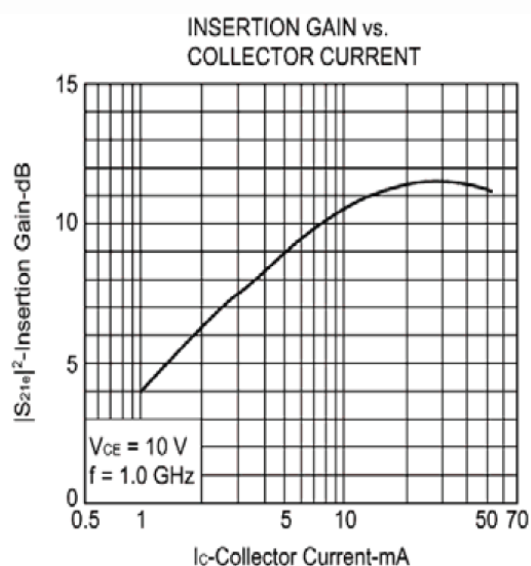
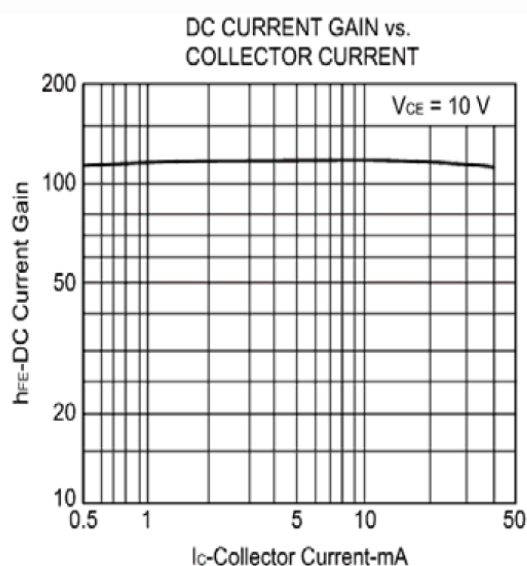
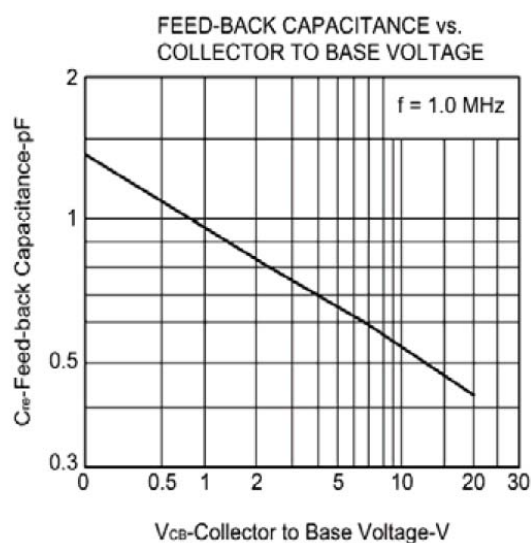
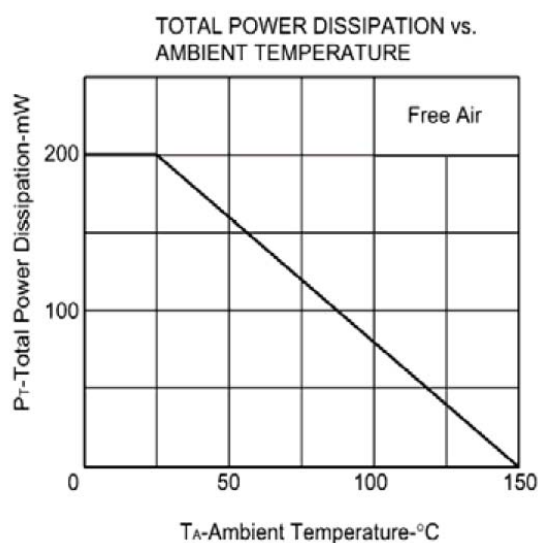
Electrical Characteristics

($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Conditions	Min	Typ	Max	Unit
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=1\text{mA}$, $I_B=0\text{mA}$)	12	-	-	V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=10\text{uA}$, $I_E=0\text{mA}$)	20	-	-	V
$V_{CE(sat)}$	Collector-Emitter Breakdown Voltage ($I_C=50\text{mA}$, $I_B=5\text{mA}$)	-	-	200	mV
I_{CBO}	Collector Cut-off Current ($V_{CB}=10\text{V}$, $I_E=0\text{mA}$)	-	-	1	μA
I_{EBO}	Emitter Cut-off Current ($V_{EB}=1\text{V}$, $I_C=0\text{mA}$)	-	-	1	μA
h_{FE}	DC Current Gain ($V_{CE}=3\text{V}$, $I_C=10\text{mA}$)	82	-	270	-
f_T	Transition Frequency ($V_{CE}=10\text{V}$, $I_C=20\text{mA}$)	-	7	-	GHz
N_F	Noise Figure ($V_{CE}=10\text{V}$, $I_C=7\text{mA}$, $f=1\text{GHz}$)	-	-	2	dB

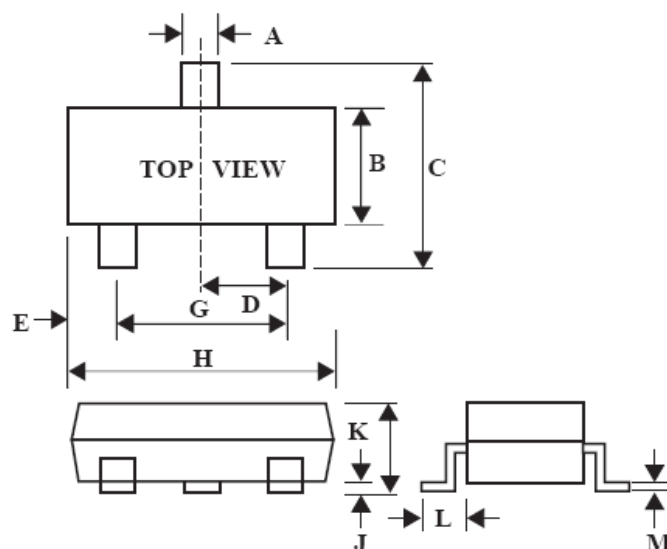
Note 1: Pulse Test: Pulse Width $\leq 350\text{ us}$, Duty Cycle $\leq 2.0\%$

Typical Performance Characteristics



Package Dimension

SOT-23



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.35	0.51	0.014	0.020
B	1.19	1.40	0.047	0.055
C	2.10	3.00	0.083	0.118
D	0.85	1.05	0.033	0.041
E	0.46	1.00	0.018	0.039
G	1.70	2.10	0.067	0.083
H	2.70	3.10	0.106	0.122
J	0.01	0.13	0.000	0.005
K	0.89	1.10	0.035	0.043
L	0.30	0.61	0.011	0.024
M	0.076	0.25	0.002	0.010

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